

HIGH CURRENT APPLICATION.

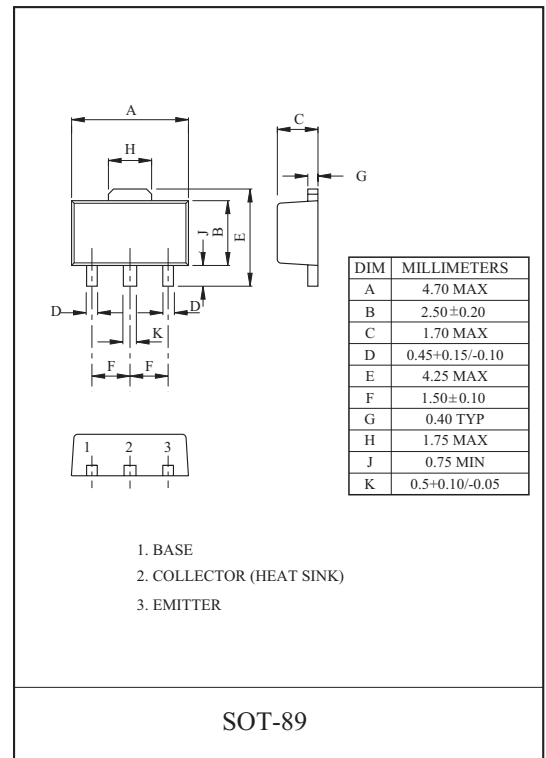
FEATURES

- High Voltage : $V_{CEO}=-120V$.
- High Transition Frequency : $f_T=120MHz(Typ.)$.
- 1W(Monunted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4373.
- Suffix U : Qualified to AEC-Q101.
ex) KTA1661-RTK/PU

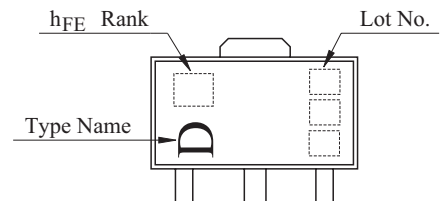
MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
	P_C^*	1	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

P_C^* : KTA1661 mounted on ceramic substrate (250mm²x0.8t)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-120V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5.0	-	-	V
DC Current Gain	h_{FE} (Note)	$V_{CE}=-5V, I_C=-100mA$	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$	-	-	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5V, I_C=-500mA$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-100mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	-	30	pF

Note : h_{FE} Classification O:80 160, Y:120 240

